Drain Currents PMOS: $I_{D1,2} = 12.5 \mu A$ $I_{D5} = 25 \mu A$ $I_{D3,4} = 12.5 \mu A$ $I_{D3A,4A} = 12.5 \mu A$ $I_{D3-2} = 25 = \frac{30}{2} \left(\frac{W}{L}\right) = \left(\frac{0.1}{2}\right)^2$ $\left(\frac{W}{L}\right) = \frac{2(25)}{30(0.1)^2} = \frac{166}{2}$

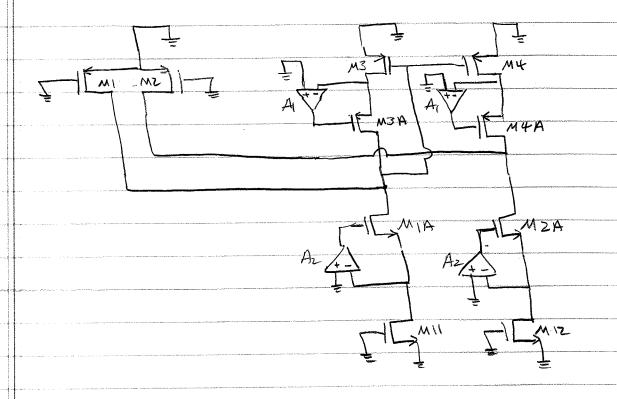
NMOS: ID11,12 = 25MA ID1A, ZA = 12.5MA

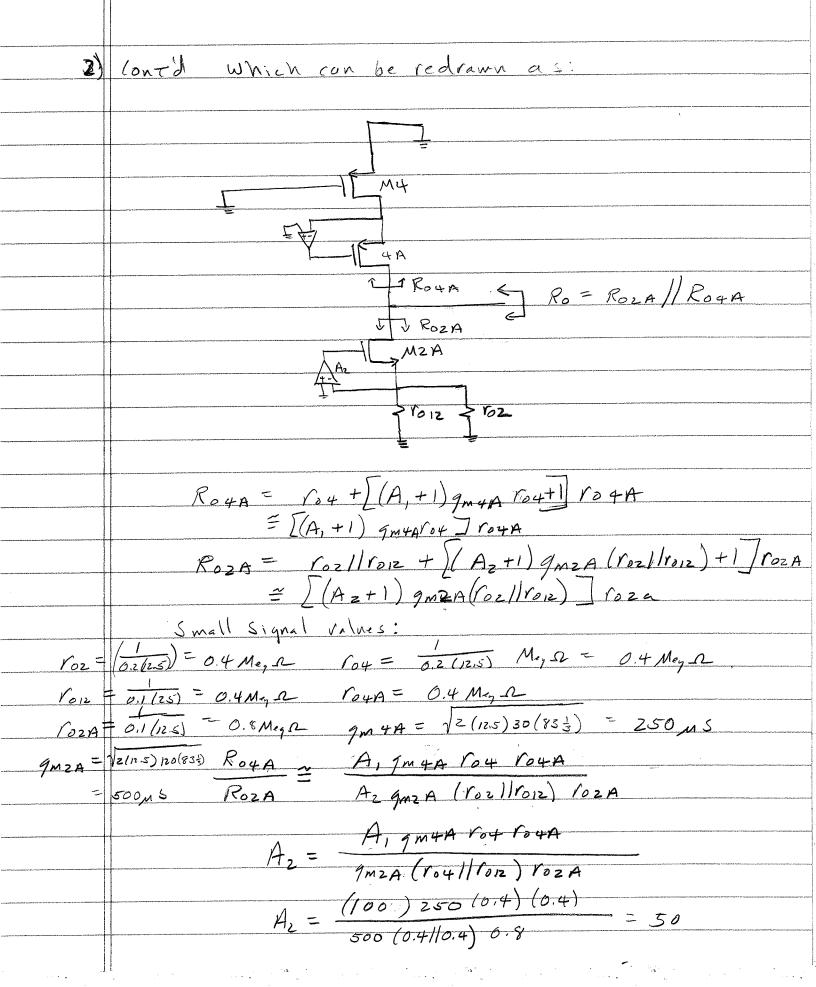
 $F_{PII,12} = 25 = \frac{120}{2} \left(\frac{W}{L}\right)_{II,12} \left(0.1\right)^{2}$ $\left(\frac{W}{L}\right)_{II,12} = \frac{(2i25)}{120(0.1)^{2}} = 41.\frac{2}{5}$ All 0 the NMOS are helf as wide $\rightarrow 20.\frac{5}{6}$

All other PMOS are half as wide -> 83 =



2) In the small signal analysis of our put
resistance, the source of transistors MI + MZ
may be can sidered to be small signal ground which
greatly simplifies the calculation of our put







3) What is approx gain

Av= 6m Ro = gm, Ro

Ro= ROZA // ROYA

RO4A = ROZA = 50(500) (0.2) 0.8 = 14x109 52 52

Po = 14,000 Mag C gm, = V2 (12.5)(30) (83=) = 250,15

Av= 250 (40,000) = 106 Very high!